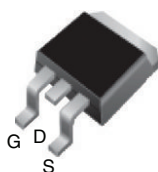


E Series Power MOSFET

D²PAK (TO-263)


N-Channel MOSFET

FEATURES

- 4th generation E series technology
- Low figure-of-merit (FOM) $R_{on} \times Q_g$
- Low effective capacitance ($C_{o(er)}$)
- Reduced switching and conduction losses
- Avalanche energy rated (UIS)
- Kelvin connection for reduced gate noise
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
 - High-intensity discharge (HID)
 - Fluorescent ballast lighting
- Industrial
 - Welding
 - Induction heating
 - Motor drives
 - Battery chargers
 - Solar (PV inverters)

PRODUCT SUMMARY

V_{DS} (V) at T_J max.	700	
$R_{DS(on)}$ typ. (Ω) at 25 °C	$V_{GS} = 10$ V	0.087
Q_g max. (nC)	62	
Q_{gs} (nC)	16	
Q_{gd} (nC)	15	
Configuration	Single	

ORDERING INFORMATION

Package	D ² PAK (TO-263)
Lead (Pb)-free and halogen-free	SiHB100N65E-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	650	V
Gate-source voltage	V_{GS}	± 30	
Continuous drain current ($T_J = 150$ °C)	V_{GS} at 10 V	$T_C = 25$ °C	A
		$T_C = 100$ °C	
Pulsed drain current ^a	I_{DM}	63	W/°C
Linear derating factor		1.47	
Single pulse avalanche energy ^b	E_{AS}	127	mJ
Maximum power dissipation	P_D	208	W
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +150	°C
Drain-source voltage slope	dv/dt	100	V/ns
Reverse diode dv/dt ^c		11	

Notes

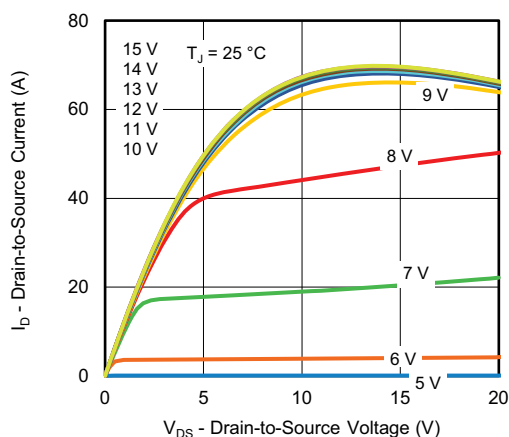
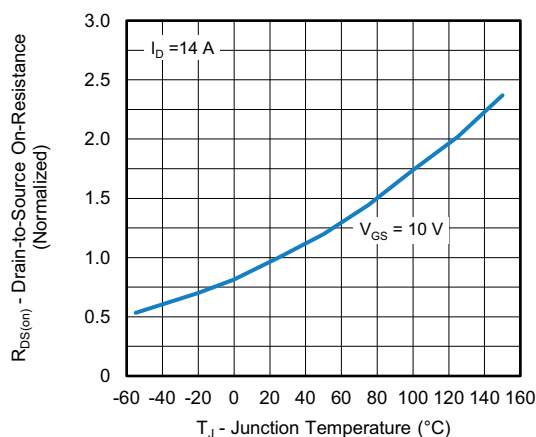
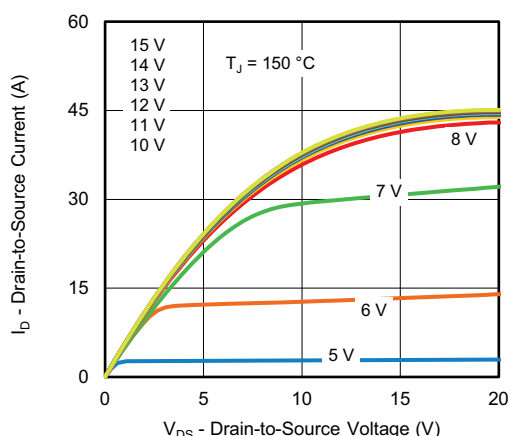
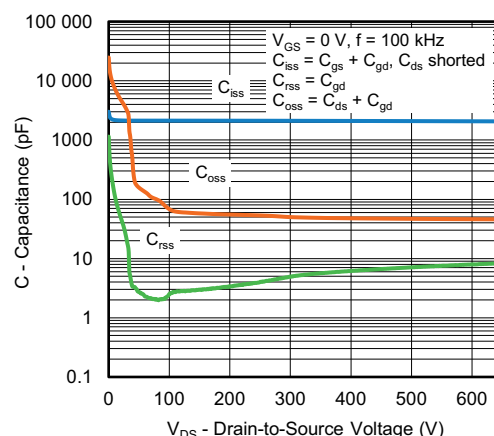
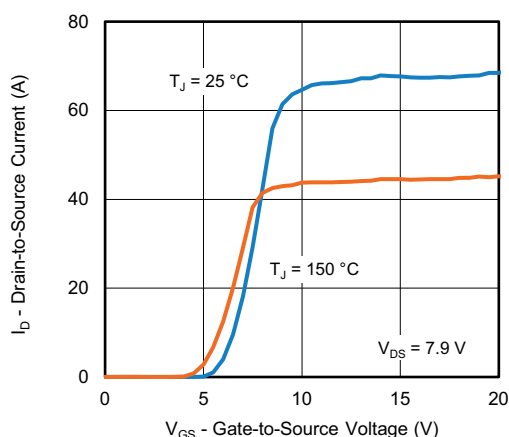
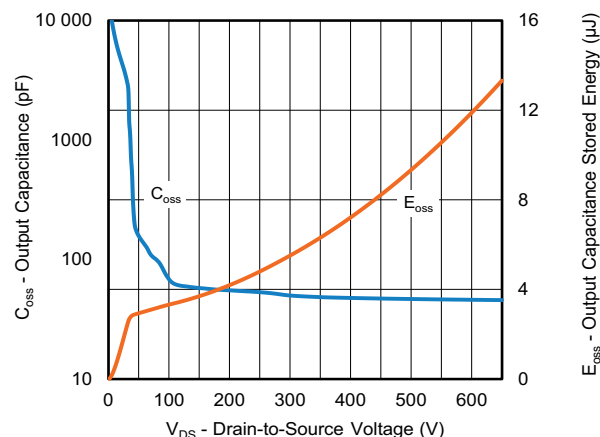
- Repetitive rating; pulse width limited by maximum junction temperature
- $V_{DD} = 140$ V, starting $T_J = 25$ °C, $L = 28.2$ mH, $R_g = 25$ Ω , $I_{AS} = 3.0$ A
- $I_{SD} \leq I_D$, $di/dt = 100$ A/ μ s, starting $T_J = 25$ °C

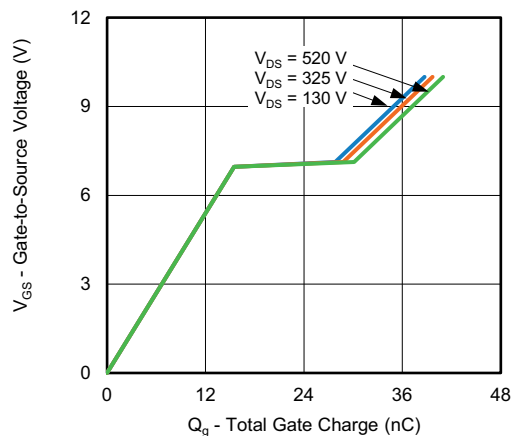
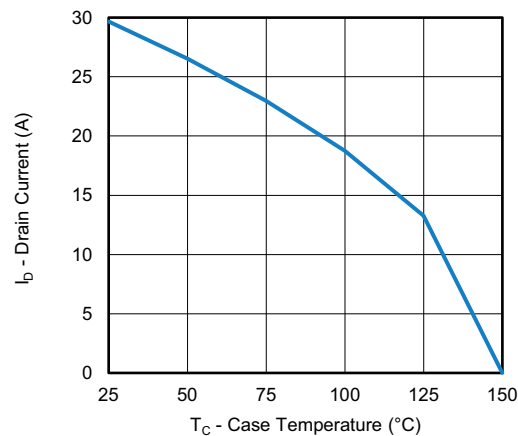
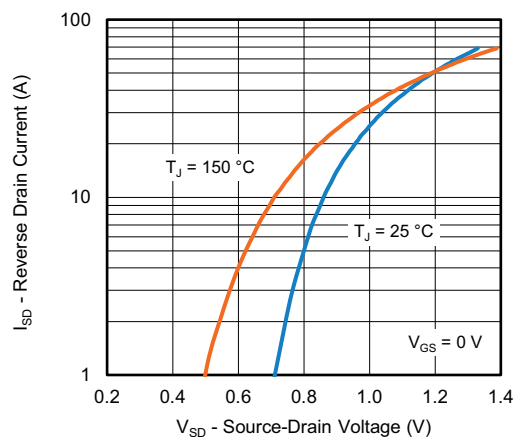
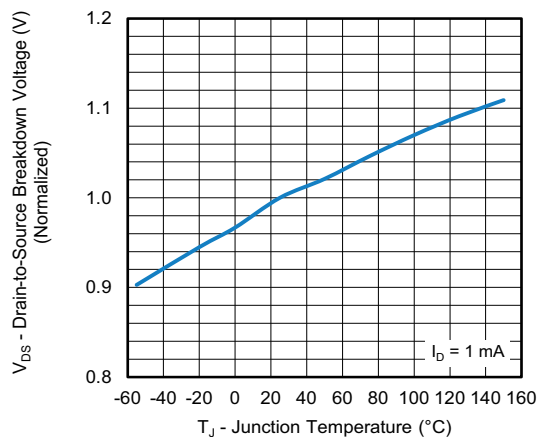
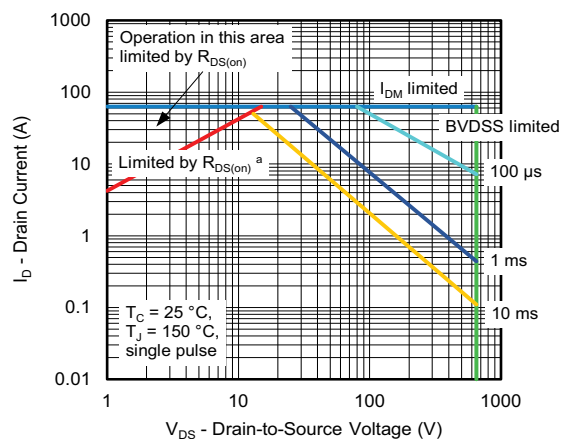
**THERMAL RESISTANCE RATINGS**

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R_{thJA}	-	62	°C/W
Maximum junction-to-case (drain)	R_{thJC}	-	0.6	

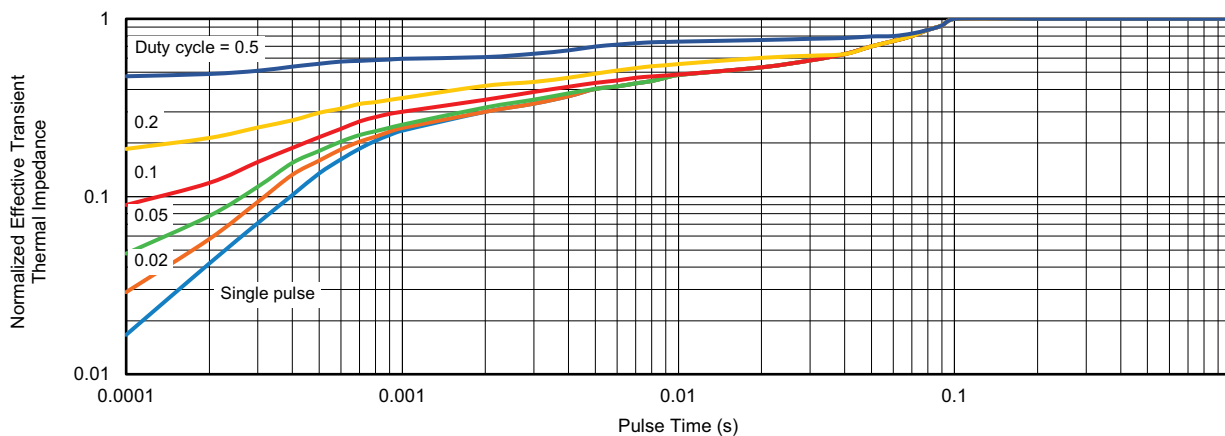
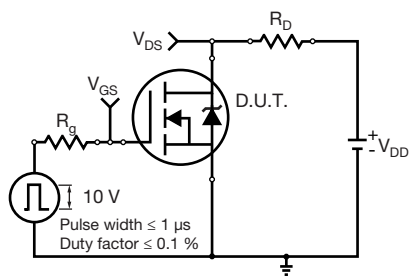
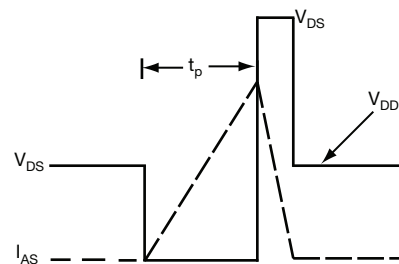
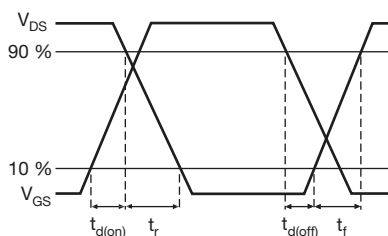
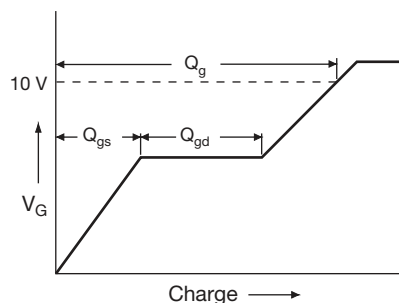
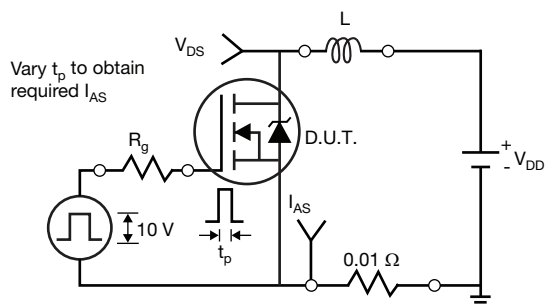
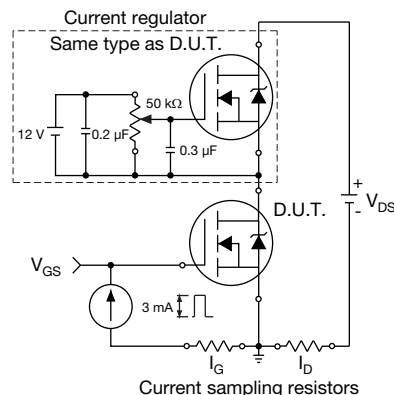
SPECIFICATIONS ($T_J = 25\text{ °C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		650	-	-	V
V _{DS} temperature coefficient	ΔV _{DS} /T _J	Reference to 25 °C, I _D = 1 mA		-	0.68	-	V/°C
Gate-source threshold voltage (N)	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		3.0	-	5.0	V
Gate-source leakage	I _{GSS}	V _{GS} = ± 20 V		-	-	± 100	nA
		V _{GS} = ± 30 V		-	-	± 1	μA
Zero gate voltage drain current	I _{DSS}	V _{DS} = 650 V, V _{GS} = 0 V		-	-	1	μA
		V _{DS} = 520 V, V _{GS} = 0 V, T _J = 125 °C		-	-	10	
Drain-source on-state resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 12 A	-	0.087	0.100	Ω
Forward transconductance ^a	g _{fs}	V _{DS} = 8 V, I _D = 14 A		-	12	-	S
Dynamic							
Input capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 100 V, f = 1 MHz		-	2137	-	pF
Output capacitance	C _{Oss}			-	89	-	
Reverse transfer capacitance	C _{rss}			-	2	-	
Effective output capacitance, energy related ^a	C _{O(er)}	V _{DS} = 0 V to 400 V, V _{GS} = 0 V		-	90	-	
Effective output capacitance, time related ^b	C _{O(tr)}			-	633	-	
Total gate charge	Q _g	V _{GS} = 10 V	I _D = 14 A, V _{DS} = 520 V	-	41	62	nC
Gate-source charge	Q _{gs}			-	16	-	
Gate-drain charge	Q _{gd}			-	15	-	
Turn-on delay time	t _{d(on)}	V _{DD} = 520 V, I _D = 14 A, V _{GS} = 10 V, R _g = 9.1 Ω		-	28	56	ns
Rise time	t _r			-	68	136	
Turn-off delay time	t _{d(off)}			-	50	100	
Fall time	t _f			-	32	64	
Gate input resistance	R _g	f = 1 MHz, Open Drain		0.5	1.1	2.2	Ω
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I _S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	30	A
Pulsed diode forward current	I _{SM}			-	-	63	
Diode forward voltage	V _{SD}	T _J = 25 °C, I _S = 14 A, V _{GS} = 0 V		-	-	1.2	V
Reverse recovery time	t _{rr}	T _J = 25 °C, I _F = I _S = 14A, di/dt = 100 A/μs, V _R = 25 V		-	362	724	ns
Reverse recovery charge	Q _{rr}			-	5.0	10	μC
Reverse recovery current	I _{RRM}			-	22	-	A

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics

Fig. 4 - Normalized On-Resistance vs. Temperature

Fig. 2 - Typical Output Characteristics

Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

Fig. 3 - Typical Transfer Characteristics

Fig. 6 - C_{oss} and E_{oss} vs. V_{DS}


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

Fig. 10 - Maximum Drain Current vs. Case Temperature

Fig. 8 - Typical Source-Drain Diode Forward Voltage

Fig. 11 - Temperature vs. Drain-to-Source Voltage

Fig. 9 - Maximum Safe Operating Area
Note

a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified


Fig. 12 - Normalized Transient Thermal Impedance, Junction-to-Case

Fig. 13 - Switching Time Test Circuit

Fig. 16 - Unclamped Inductive Waveforms

Fig. 14 - Switching Time Waveforms

Fig. 17 - Basic Gate Charge Waveform

Fig. 15 - Unclamped Inductive Test Circuit

Fig. 18 - Gate Charge Test Circuit

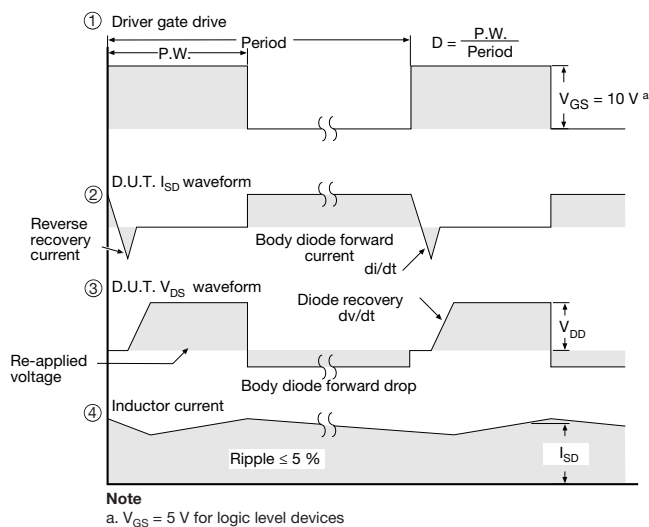
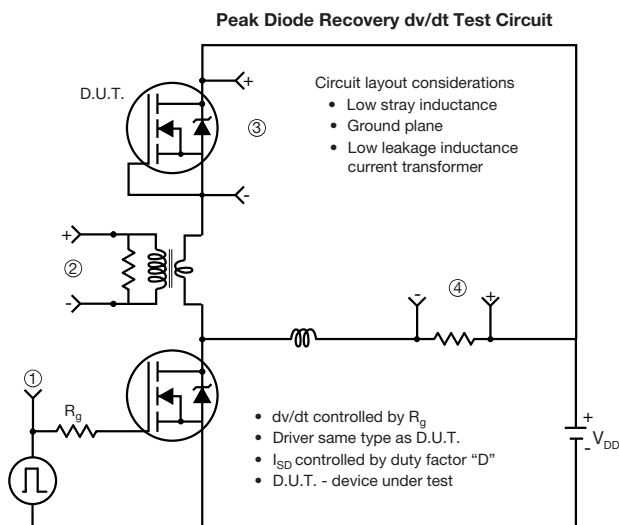


Fig. 19 - For N-Channel

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	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

[Return to Index](#)



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